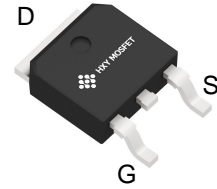




## Description

The IPD30N06S3-24 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



TO-252-2L

## General Features

$V_{DS} = 60V$   $I_D = 30A$

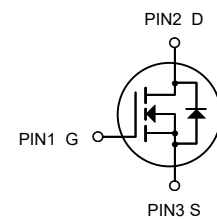
$R_{DS(ON)} < 26m\Omega$  @  $V_{GS} = 10V$

## Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

## Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IPD30N06S3-24	TO-252-2L	HXY MOSFET	2500

## Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	30	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	15	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	46	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	25.5	mJ
$I_{AS}$	Avalanche Current	22.6	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation <sup>4</sup>	34.7	W
$P_D @ T_A = 25^\circ C$	Total Power Dissipation <sup>4</sup>	2	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	3.6	$^\circ C/W$



**Electrical Characteristics ( $T_J=25^{\circ}\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	$BV_{DSS}$ Temperature Coefficient	Reference to $25^{\circ}\text{C}$ , $I_D=1\text{mA}$	---	0.063	---	$\text{V}/^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=15A$	---	22	26	m $\Omega$
		$V_{GS}=4.5V, I_D=10A$	---	30	38	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	---	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.24	---	$\text{mV}/^{\circ}\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=48V, V_{GS}=0V, T_J=25^{\circ}\text{C}$	---	---	1	$\mu\text{A}$
		$V_{DS}=48V, V_{GS}=0V, T_J=55^{\circ}\text{C}$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=5V, I_D=15A$	---	17	---	S
$R_g$	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	3.2	---	$\Omega$
$Q_g$	Total Gate Charge (4.5V)	$V_{DS}=48V, V_{GS}=4.5V, I_D=12A$	---	12.6	---	nC
$Q_{gs}$	Gate-Source Charge		---	3.2	---	
$Q_{gd}$	Gate-Drain Charge		---	6.3	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=30V, V_{GS}=10V, R_G=3.3\Omega, I_D=10A$	---	8	---	ns
$T_r$	Rise Time		---	14.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	24.4	---	
$T_f$	Fall Time		---	4.6	---	
$C_{iss}$	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	1378	---	pF
$C_{oss}$	Output Capacitance		---	86	---	
$C_{riss}$	Reverse Transfer Capacitance		---	64	---	
$I_S$	Continuous Source Current <sup>1,5</sup>	$V_G=V_D=0V, \text{Force Current}$	---	---	23	A
$I_{SM}$	Pulsed Source Current <sup>2,5</sup>		---	---	46	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=1A, T_J=25^{\circ}\text{C}$	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu\text{s}$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=22.6A$
- 4.The power dissipation is limited by  $150^{\circ}\text{C}$  junction temperature
- 5.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.



### Typical Characteristics

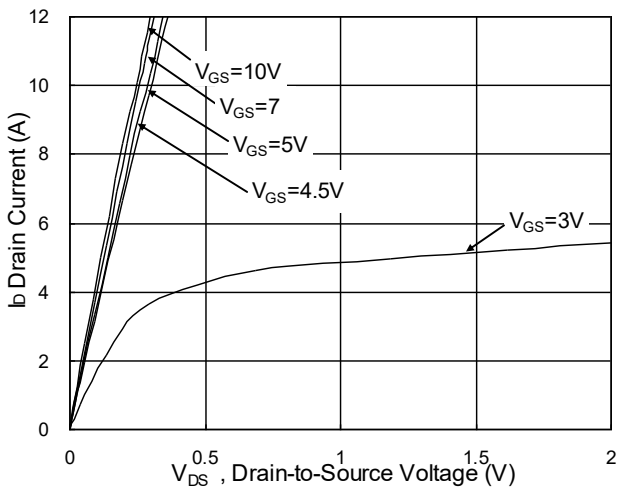


Fig.1 Typical Output Characteristics

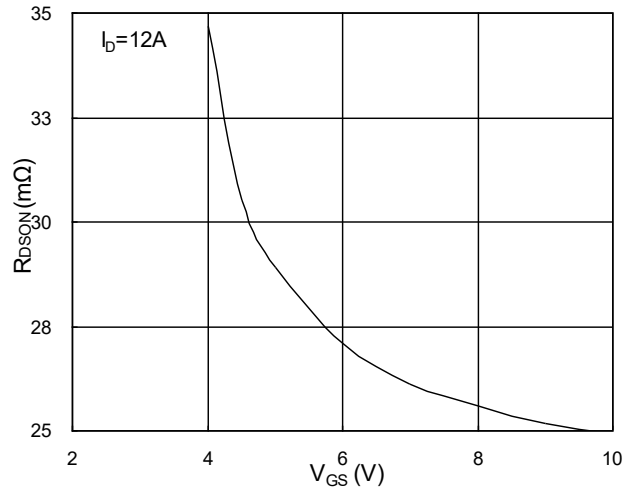


Fig.2 On-Resistance v.s Gate-Source

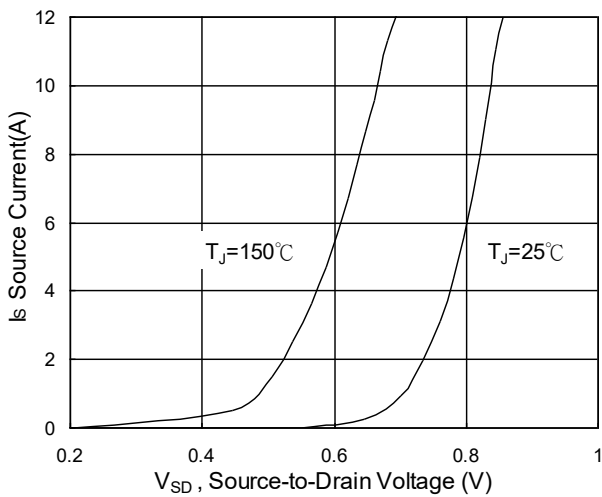


Fig.3 Forward Characteristics of Reverse

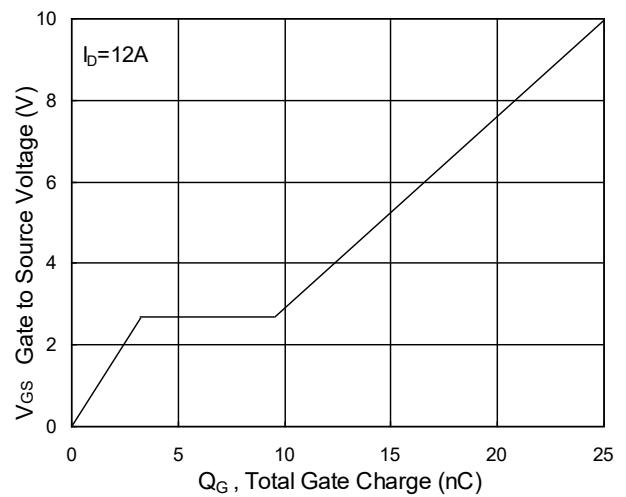


Fig.4 Gate-Charge Characteristics

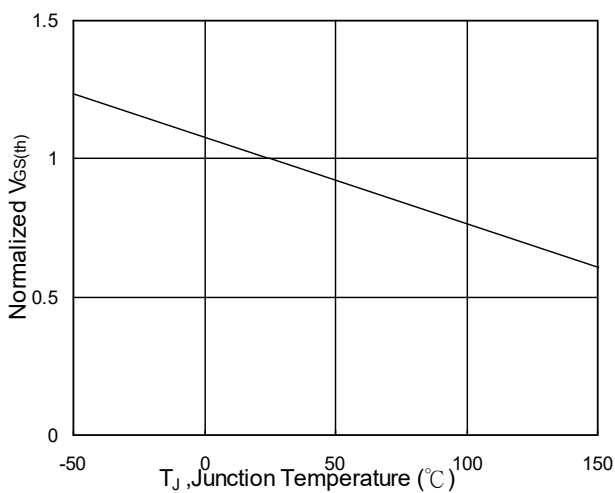


Fig.5 Normalized V<sub>GS(th)</sub> v.s T<sub>J</sub>

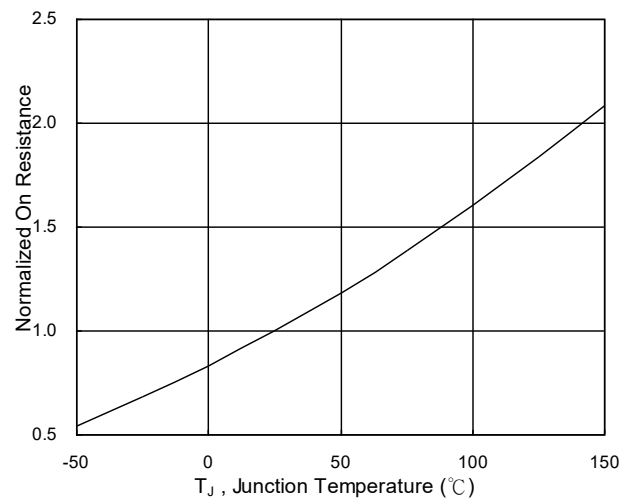


Fig.6 Normalized R<sub>DS(on)</sub> v.s T<sub>J</sub>

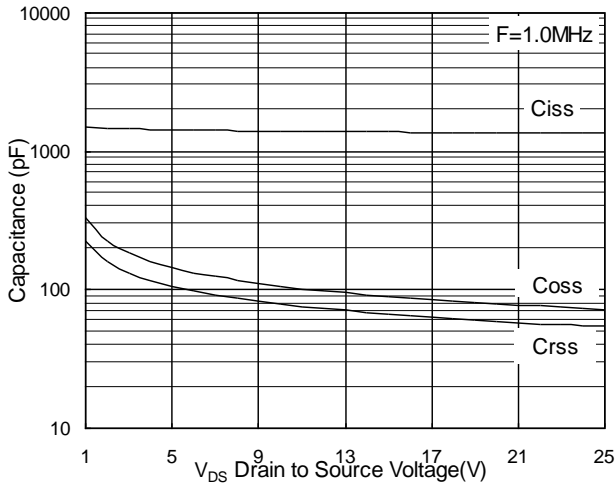


Fig.7 Capacitance

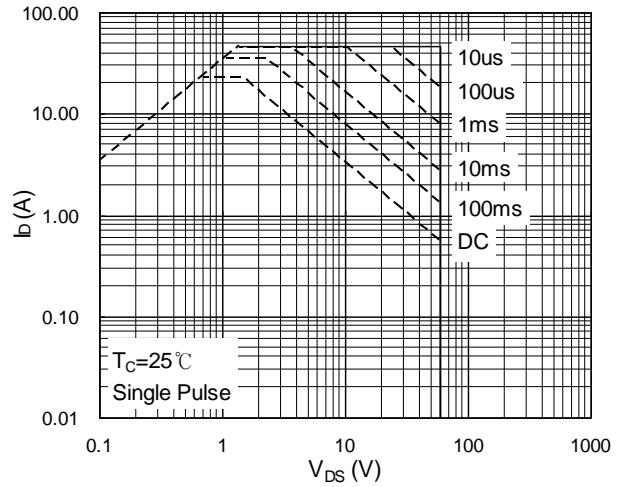


Fig.8 Safe Operating Area

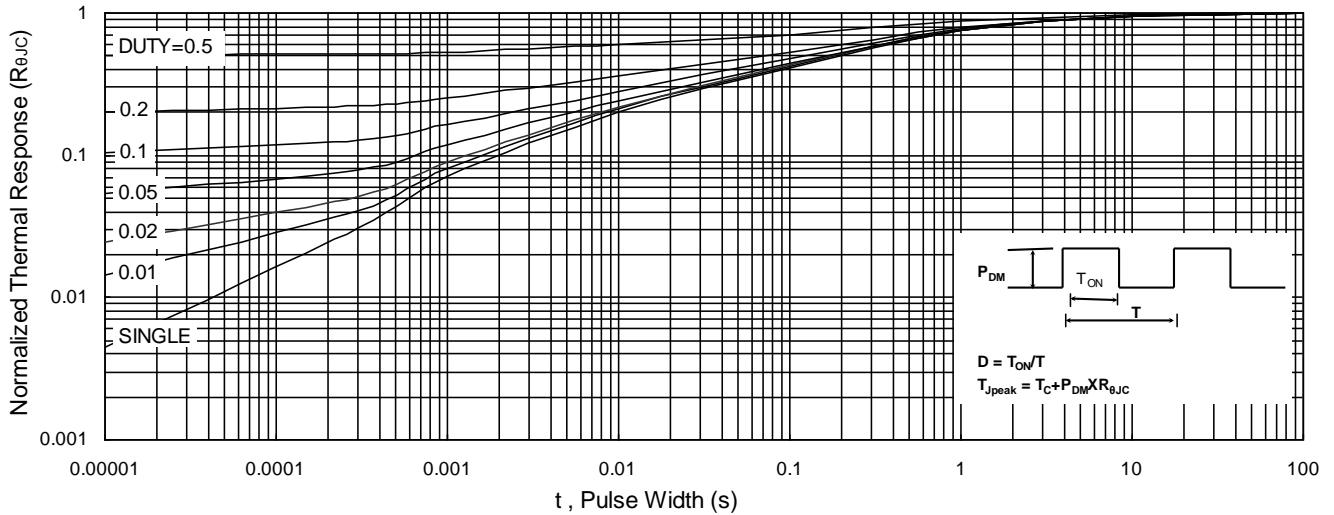


Fig.9 Normalized Maximum Transient Thermal Impedance

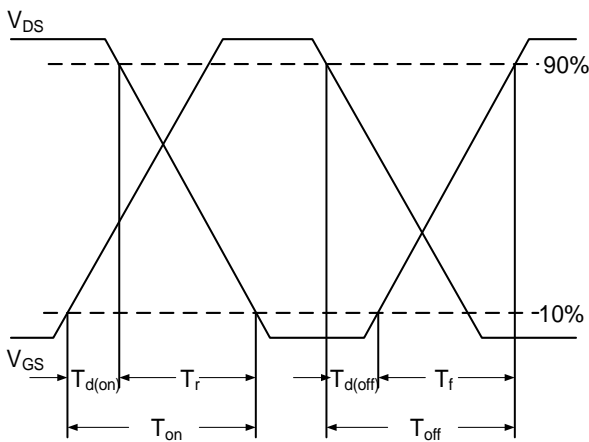


Fig.10 Switching Time Waveform

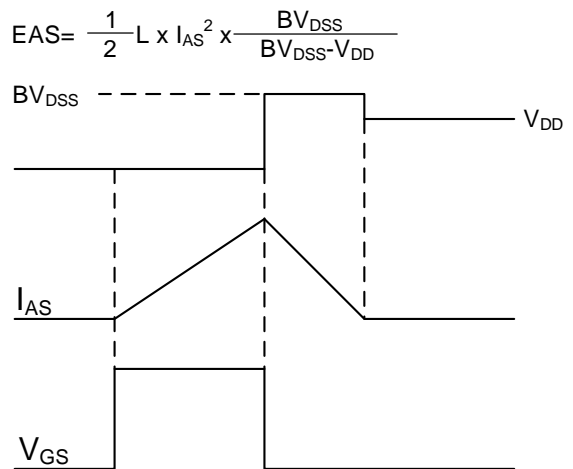


Fig.11 Unclamped Inductive Waveform





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